

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Kuniaki YAGI, et al.

Appln. No.: Not Yet Assigned

Confirmation No.: Not Yet Assigned

Group Art Unit: Not Yet Assigned

Filed: January 18, 2002

Examiner: Not Yet Assigned

For: SINGLE CRYSTAL SiC AND METHOD OF PRODUCING THE SAME AS WELL AS
SiC SEMICONDUCTOR DEVICE AND SiC COMPOSITE MATERIAL

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please enter the following amended claims:

6. A single crystal SiC, wherein:

the single crystal SiC is obtained by a method claimed in claim 1, and

the planar defect density of a topmost surface falls within a range not higher than $10^3/cm^2$.

7. A single crystal SiC, comprising:

single crystal SiC obtained by a method claimed in claim 1, and

another SiC deposited on the single crystal SiC by the vapor phase growth method or the liquid phase growth method.

10. A SiC composite material, comprising:

single crystal SiC produced by a method claimed in claim 1, and

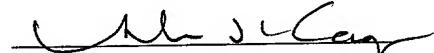
diamond or GaN formed on the single crystal SiC.

PRELIMINARY AMENDMENT
Attorney Docket No.: Q68148

REMARKS

Accordingly, early and favorable consideration of the presently pending claims is respectfully requested.

Respectfully submitted,



Alan J. Kasper
Registration No. 25,426

SUGHRUE MION, PLLC
2100 Pennsylvania Avenue, N.W.
Washington, D.C. 20037-3213
Telephone: (202) 293-7060
Facsimile: (202) 293-7860
AJK/rwl
Date: January 18, 2002

AUGUST 10 2002
U.S. PATENT AND TRADEMARK OFFICE

PRELIMINARY AMENDMENT
Attorney Docket No.: Q68148

APPENDIX

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

The claims are amended as follows:

6. A single crystal SiC, wherein:

the single crystal SiC is obtained by a method claimed in ~~any one of~~ claims 1-through-5,

and

the planar defect density of a topmost surface falls within a range not higher than $10^3/\text{cm}^{-2}$.

7. A single crystal SiC, comprising:

single crystal SiC obtained by a method claimed in ~~any one of~~ claims 1-through-5, and

another SiC deposited on the single crystal SiC by the vapor phase growth method or the liquid phase growth method.

10. A SiC composite material, comprising:

single crystal SiC produced by a method claimed in ~~any one of~~ claims 1-through-5, and

diamond or GaN formed on the single crystal SiC.